ΡΛΝ	JIT
	SEMI
	CONDUCTOR



#### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS
Collector-Base Voltage	V <sub>CBO</sub>	60	V
Collector-Emitter Voltage	Vceo	40	V
Emitter-Base Voltage	Vebo	6	V
Collector Current (DC)	lc	200	mA
Collector Power Dissipation	PD	150	mW
Operating Junction and Storage Temperature Range	Т <sub>Ј</sub> ,Т <sub>STG</sub>	-55~150	°C
Thermal Resistance from Junction to Ambient <sup>(Note 1)</sup>	Reja	833	°C/W

Note 1 : Mounted on FR4 PCB at 1 inch square copper pad.



#### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
OFF Characteristics							
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub> Ic= 1mA, I <sub>B</sub> = 0A		40	-	-	V	
Collector-Base Breakdown Voltage	ВVсво	I <sub>C</sub> = 10uA, I <sub>E</sub> = 0A	60	-	-	V	
Emitter-Base Breakdown Voltage	ВV <sub>ЕВО</sub>	I <sub>E</sub> = 10uA, I <sub>C</sub> = 0A	6	-	-	V	
Base Cutoff Current	I <sub>BL</sub>	$V_{CE}$ = 30V, $V_{EB}$ = 3V	-	-	50	nA	
Collector Cutoff Current	ICEX	$V_{CE}$ = 30V, $V_{EB}$ = 3V	-	-	50	nA	
ON characteristics							
	hfe	V <sub>CE</sub> = 1V, I <sub>C</sub> = 0.1mA	40	-	-		
DC Current Gain <sup>(Note 2)</sup>		V <sub>CE</sub> = 1V, I <sub>C</sub> = 1mA	70	-	-		
		V <sub>CE</sub> = 1V, I <sub>C</sub> = 10mA	100	-	300		
		$V_{CE}$ = 1V, I <sub>C</sub> = 50mA	60	-	-		
		V <sub>CE</sub> = 1V, I <sub>C</sub> = 100mA	30	-	-		
Collector-Emitter Saturation	Ň	$I_{C}$ = 10mA, $I_{B}$ = 1mA	-	-	200		
Voltage <sup>(Note 2)</sup>	VCE(SAT)	Ic= 50mA, Iв= 5mA	-	-	300	mV	
Base-Emitter Saturation voltage <sup>(Note 2)</sup>	VBE(SAT)	Ic= 10mA, I <sub>B</sub> = 1mA	650	-	850		
		Ic= 50mA, I <sub>B</sub> = 5mA	-	-	950	mV	
Collector-Base Capacitance	Ссво	$V_{CB}$ = 5V I <sub>E</sub> = 0A,			1	ъĘ	
		f=1MHz	-	-	4	рг	
Emitter-Base Capacitance	Сево	$V_{EB}=0.5V\ I_C=0A,$	_	_	8	рF	
		f=1MHz	-	-	U	Ч	
Delay Time	Td	Vcc= 3V, V <sub>BE</sub> = 0.5V	-	-	35	nS	
Rise Time	Tr	Ic= 10mA, I <sub>B</sub> = 1mA	-	-	35	nS	
Storage Time	Ts	Ts Vcc= 3V, Ic= 10mA   Tf I <sub>B1</sub> = I <sub>B2</sub> = 1mA		-	200	nS	
Fall Time	Tf			-	50		

Note 2 : Pulse Test: Pulse Width < 300uS , Duty Cycle < 2%

### **MMBT3904TB**









#### **Product and Packing Information**

Part No.	Package Type	Packing Type	Marking
MMBT3904TB	SOT-523	4K pcs / 7" reel	4E

#### **Packaging Information & Mounting Pad Layout**





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